Abstracts

Measuring transistor dynamic load lines and breakdown currents under large-signal high-frequency operating conditions

J. Verspecbt and D. Schreurs. "Measuring transistor dynamic load lines and breakdown currents under large-signal high-frequency operating conditions." 1998 MTT-S International Microwave Symposium Digest 98.3 (1998 Vol. III [MWSYM]): 1495-1498.

The "Nonlinear Network Measurement System" accurately measures dynamic loadlines and breakdown currents of microwave transistors under high-frequency large-signal operating conditions. This measurement capability allows the designer to find optimal operating conditions for a given device without the need for large-signal models. Measuring RF breakdown currents allows the designer to tackle reliability issues in a way not possible before.

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